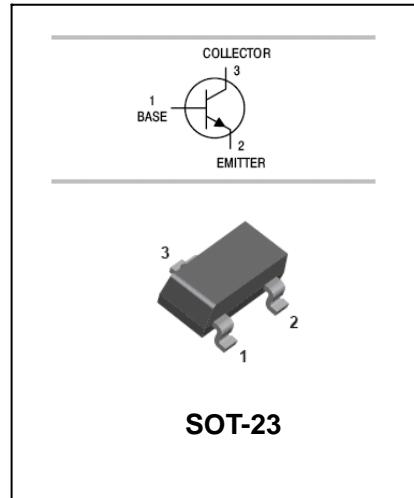


NPN Transistors

Features

- For general AF applications.
- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.



Package Code

Absolute Maximum Ratings Ta = 25°C

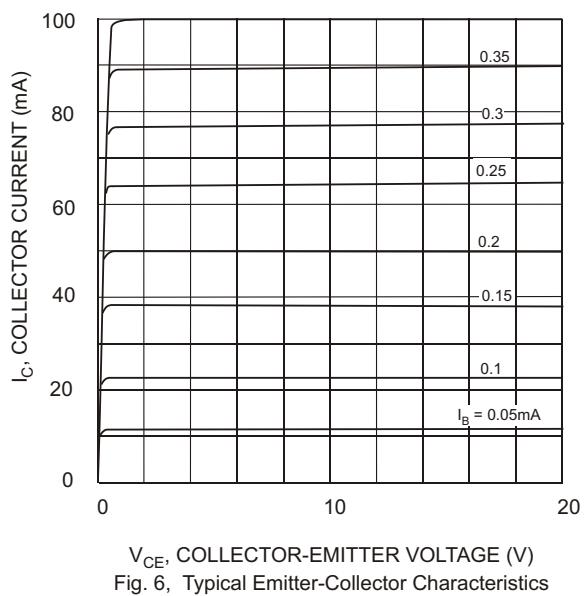
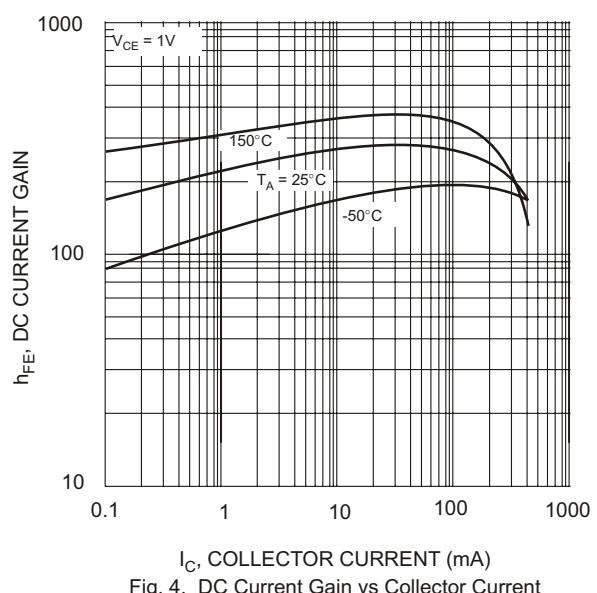
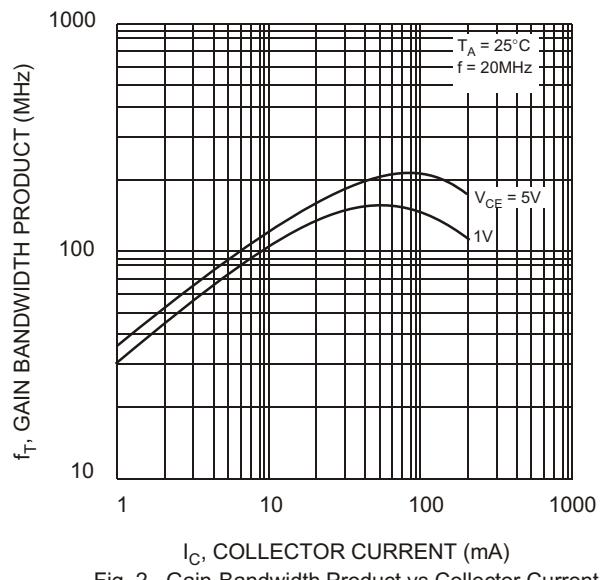
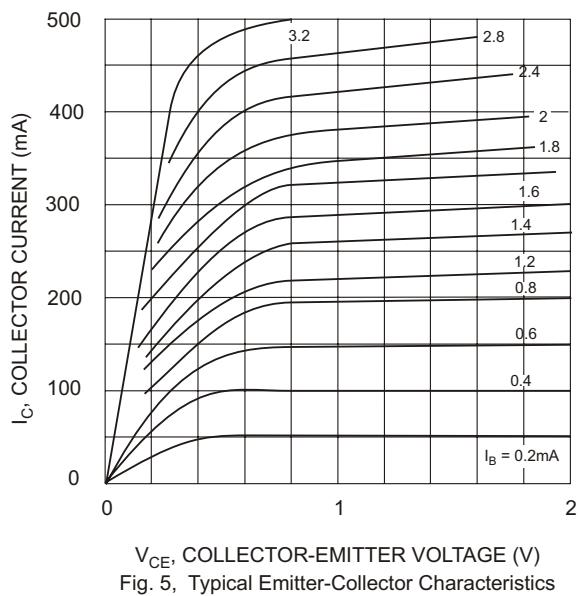
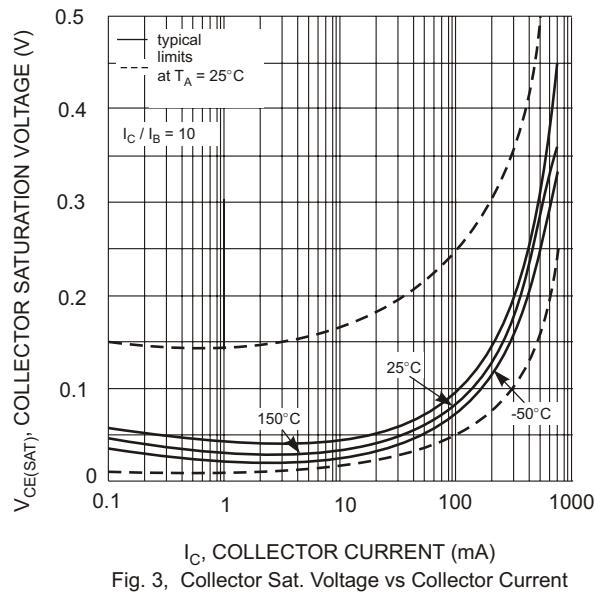
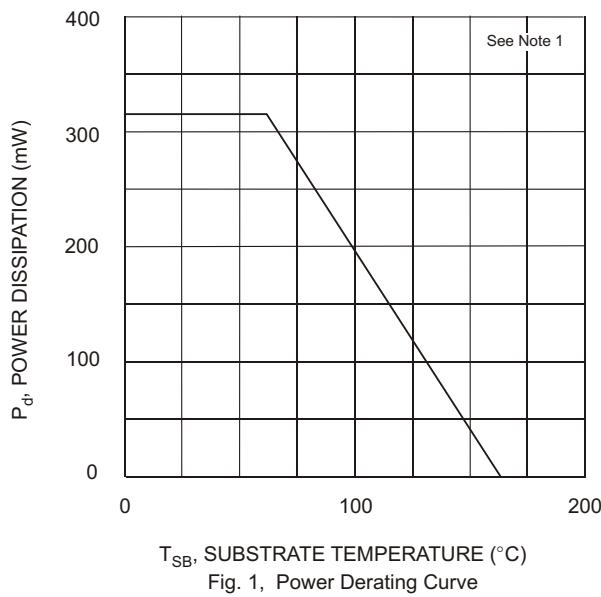
Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	50	V
Collector-emitter voltage	V _{CEO}	45	V
Emitter-base voltage	V _{EBO}	5	V
Collector current (DC)	I _C	500	mA
power dissipation	P _D	300	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	V _{CBO}	I _C = 10 μA, V _{BE} = 0	50			V
Collector-to-emitter breakdown voltage	V _{CEO}	I _C = 10 mA, I _B = 0	45			V
Emitter-to-base breakdown voltage	V _{EBO}	I _E = 1 mA, I _C = 0	5			V
Collector cutoff current	I _{CES}	V _{CB} = 45 V, V _{BE} = 0			100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = 4 V, I _C = 0			100	nA
DC current gain *	h _{FE}	I _C = 100 mA, V _{CE} = 1 V	100		600	
		I _C = 500 mA, V _{CE} = 1 V	40			
Collector saturation voltage *	V _{CE(sat)}	I _C = 500 mA, I _B = 50 mA			0.7	V
Base emitter on voltage	V _{BE}	V _{CE} =1V, I _C =500mA			1.2	V
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		10		pF
Transition frequency	f _T	I _C = 10 mA, V _{CE} = 5 V, f = 100 MHz	100			MHz

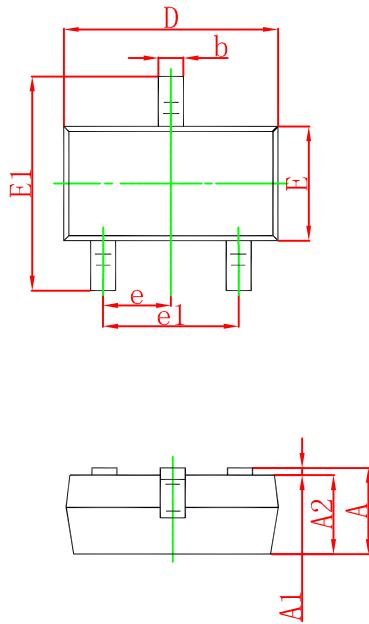
Marking

NO.	BC817-16	BC817-25	BC817-40	BC817
Marking	6A	6B	6C	6D
hFE	100~250	160~400	250~600	100~600



Package Outline Dimensions (UNIT: mm)

SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°